

Spansion[®] Analog and Microcontroller Products



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Continuity of Specifications

There is no change to this document as a result of offering the device as a Spansion product. Any changes that have been made are the result of normal document improvements and are noted in the document revision summary, where supported. Future routine revisions will occur when appropriate, and changes will be noted in a revision summary.

Continuity of Ordering Part Numbers

Spansion continues to support existing part numbers beginning with "MB". To order these products, please use only the Ordering Part Numbers listed in this document.

For More Information

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ASSP

BIPOLAR

VOLTAGE DETECTOR

MB3761

■ DESCRIPTION

Designed for voltage detector applications, the Fujitsu Microelectronics MB3761 is a dual comparator with a built-in high precision reference voltage generator. Outputs are open-collector outputs and enable use of the OR-connection between both channels. Both channels have hysteresis control outputs. Because of a wide power supply voltage range and a low power supply current, the MB3761 is suitable for power supply monitors and battery backup systems.

■ FEATURES

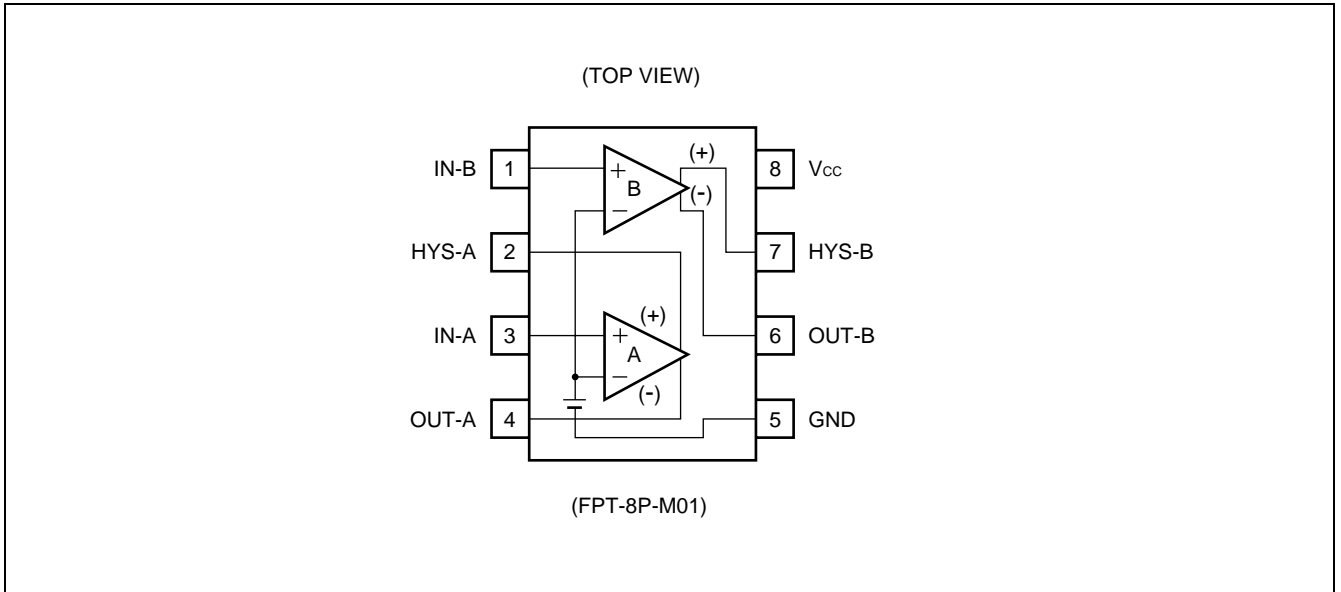
- Wide power supply voltage range: 2.5 V to 40 V
- Low power and small voltage dependency supply current: 250 μ A Typ
- Built-in stable low voltage generator: 1.20 V Typ
- Easy-to-add hysteresis characteristics.
- One type of package (SOP-8pin : 1 type)

■ APPLICATIONS

- Industrial Equipment
- Arcade Amusement etc.

MB3761

■ PIN ASSIGNMENT



■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating		Unit
		Min	Max	
Power Supply Voltage	V _{CC}	—	41	V
Output Voltage	V _O	—	41	V
Output Current	I _O	—	50	mA
Input Voltage	V _{IN}	- 0.3	+ 6.5	V
Power Dissipation	P _D	—	350 (T _A ≤ +70°C)	mW
Storage Temperature	T _{STG}	- 55	+ 125	°C

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Value		Unit
		Min	Max	
Power Supply Voltage	V _{CC}	2.5	40	V
Operating Ambient Temperature	T _A	- 20	+ 75	°C
Output Current at pin 4	I _{O4}	—	4.5	mA
Output Current at pin 6	I _{O6}	—	3.0	mA

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their representatives beforehand.

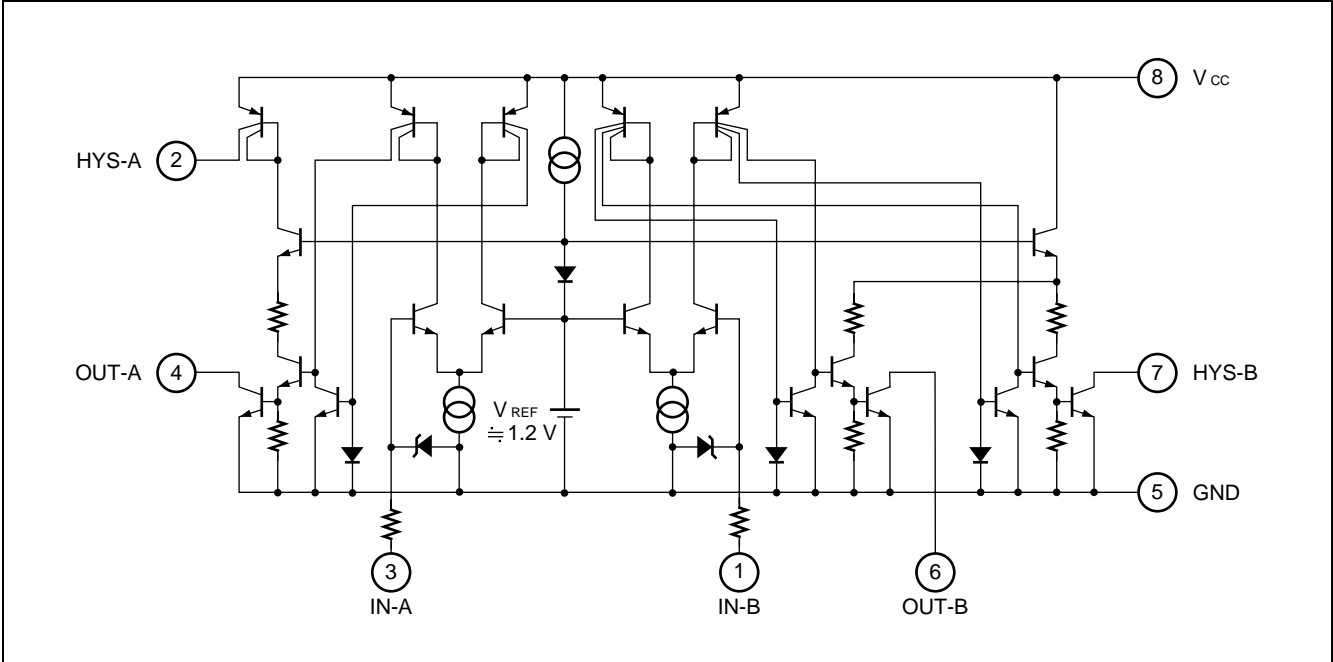
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■ ELECTRICAL CHARACTERISTICS

($T_A=+25^{\circ}\text{C}$, $V_{CC}=5\text{ V}$)

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Power Supply Voltage	ICCL	$V_{CC}=40\text{ V}$, $V_{IL}=1.0\text{ V}$	-	250	400	μA
	ICCH	$V_{CC}=40\text{ V}$, $V_{IH}=1.5\text{ V}$	-	400	600	μA
Threshold Voltage	V_{TH}	$I_O=2\text{ mA}$, $V_O=1\text{ V}$	1.15	1.20	1.25	V
Deviation of Threshold Voltage	ΔV_{TH1}	$2.5\text{ V} \leq V_{CC} \leq 5.5\text{ V}$	-	3	12	mV
	ΔV_{TH2}	$4.5\text{ V} \leq V_{CC} \leq 40\text{ V}$	-	10	40	mV
Offset Voltage between Outputs	V_{OOSA}	$I_{OA}=4.5\text{ mA}$, $V_{OA}=2\text{ V}$, $I_{HA}=20\text{ }\mu\text{A}$, $V_{HA}=3\text{ V}$	-	2.0	-	mV
	V_{OSSB}	$I_{OB}=3\text{ mA}$, $V_{OB}=2\text{ V}$, $I_{HB}=3\text{ mA}$, $V_{HB}=2\text{ V}$	-	2.0	-	mV
Temperature Coefficient of Threshold Voltage	α	$-20^{\circ}\text{C} \leq T_A \leq +70^{\circ}\text{C}$	-	± 0.05	-	$\text{mV}/^{\circ}\text{C}$
Difference Voltage on Threshold Voltage between Channel	ΔV_{THAB}	-	-10	-	+10	mV
Input Current	I_{IL}	$V_{IL}=1.0\text{ V}$	-	5	-	nA
	I_{IH}	$V_{IH}=1.5\text{ V}$	-	100	500	nA
Output Leakage Current	I_{OH}	$V_O=40\text{ V}$, $V_{IL}=1.0\text{ V}$	-	-	1	μA
Hysteresis Output Leakage Current	I_{HLA}	$V_{CC}=40\text{ V}$, $V_{HA}=0\text{ V}$, $V_{IL}=1.0\text{ V}$	-	-	0.1	μA
	I_{HHB}	$V_{HB}=40\text{ V}$, $V_{IH}=1.5\text{ V}$	-	-	1	μA
Output Sink Current	I_{OLA}	$V_O=1.0\text{ V}$, $V_{IH}=1.5\text{ V}$	6	12	-	mA
	I_{OLB}	$V_O=1.0\text{ V}$, $V_{IH}=1.5\text{ V}$	4	10	-	mA
Hysteresis Current	I_{HHA}	$V_H=0\text{ V}$, $V_{IH}=1.5\text{ V}$	40	80	-	μA
	I_{HLB}	$V_H=1.0\text{ V}$, $V_{IL}=1.0\text{ V}$	4	10	-	mA
Output Saturation Voltage	V_{OLA}	$I_O=4.5\text{ mA}$, $V_{IH}=1.5\text{ V}$	-	120	400	mV
	V_{OLB}	$I_O=3.0\text{ mA}$, $V_{IH}=1.5\text{ V}$	-	120	400	mV
Hysteresis Saturation	V_{HHA}	$I_H=20\text{ }\mu\text{A}$, $V_{IH}=1.5\text{ V}$	-	50	200	mV
	V_{HLB}	$I_H=3.0\text{ mA}$, $V_{IL}=1.0\text{ V}$	-	120	400	mV
Output Delay Time	t_{PHL}	$R_L=5\text{ k}\Omega$	-	2	-	μs
	t_{PLH}	$R_L=5\text{ k}\Omega$	-	3	-	μs

EQUIVALENT CIRCUIT



OPERATIONAL DEFINITIONS

Note:

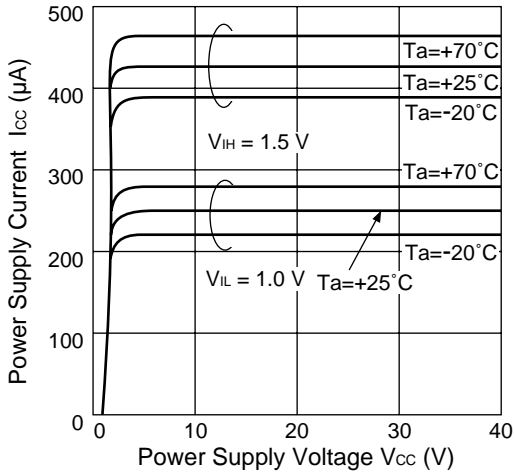
- $V_R \cong V_{TH} (\cong 1.20 \text{ V})$
- $R_2 // R_3 = \frac{R_2 R_3}{R_2 + R_3}$
- $R_5 // R_6 = \frac{R_5 R_6}{R_5 + R_6}$

$V_{IH(A)} = (1 + \frac{R_1}{R_2}) V_R$	$V_{IH(B)} = (1 + \frac{R_4}{R_5 // R_6}) V_R$
$V_{IL(A)} = (1 + \frac{R_1}{R_2 // R_3}) V_R - \frac{R_1}{R_3} V_{CC}$	$V_{IL(B)} = (1 + \frac{R_4}{R_5}) V_R$

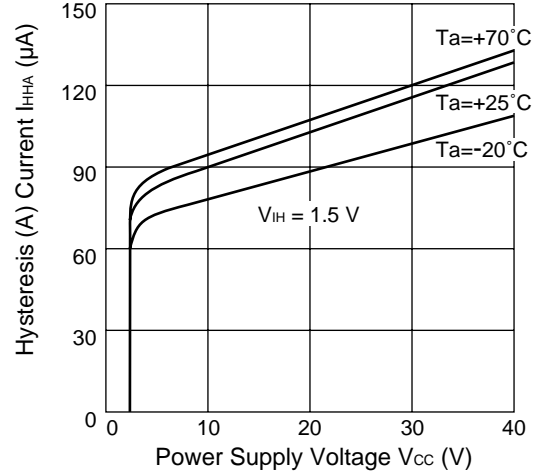
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TYPICAL PERFORMANCE CHARACTERISTICS

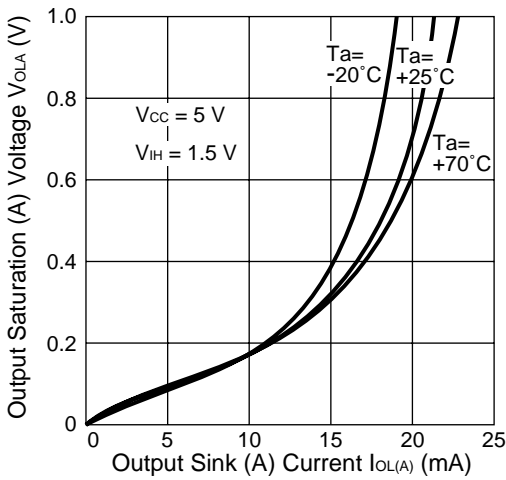
Power Supply Current vs. Power Supply Voltage



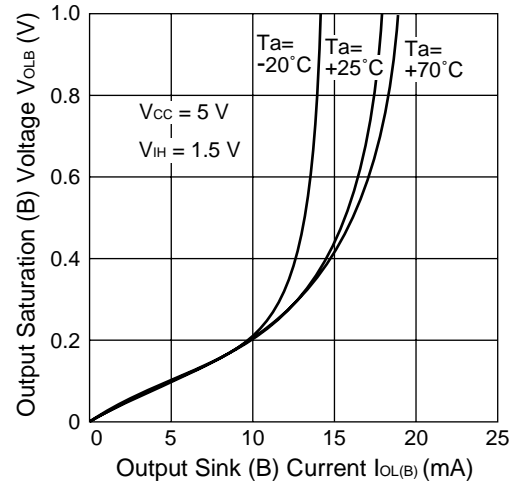
Hysteresis (A) Current vs. Power Supply Voltage



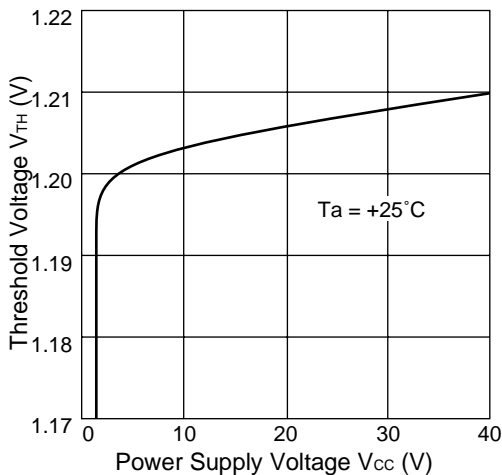
Output Saturation (A) Voltage vs. Output Sink (A) Current



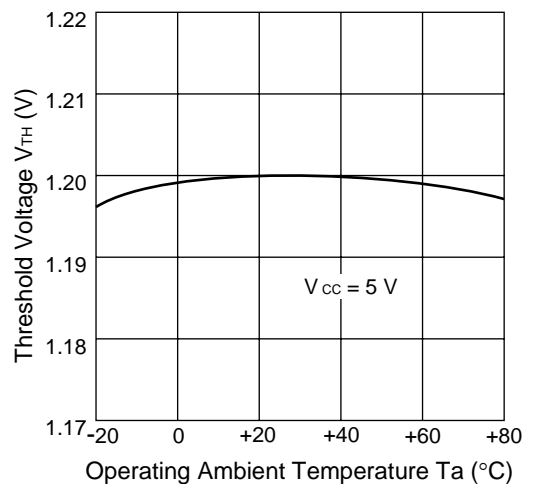
Output Saturation (B) Voltage vs. Output Sink (B) Current



Threshold Voltage vs. Power Supply Voltage



Threshold Voltage vs. Operating Ambient Temperature



APPLICATION EXAMPLES

1. Addition of Hysteresis

$$V_{IH(A)} \cong \left(1 + \frac{R_1 + R_2}{R_3}\right) V_R$$

$$V_{IL(A)} \cong \left(1 + \frac{R_2}{R_3}\right) V_R$$

$$V_{IH(B)} \cong \left(1 + \frac{R_1}{R_2}\right) V_R$$

$$V_{IL(B)} \cong \left(1 + \frac{R_1}{R_2 + R_3}\right) V_R$$

Note : All calculations occur with the output voltage at 0. The hysteresis values are adjusted for load condition and saturation voltage.

2. Voltage Detection for Alarm

$$V_{CCH} = \left(1 + \frac{R_1}{R_2}\right) V_R$$

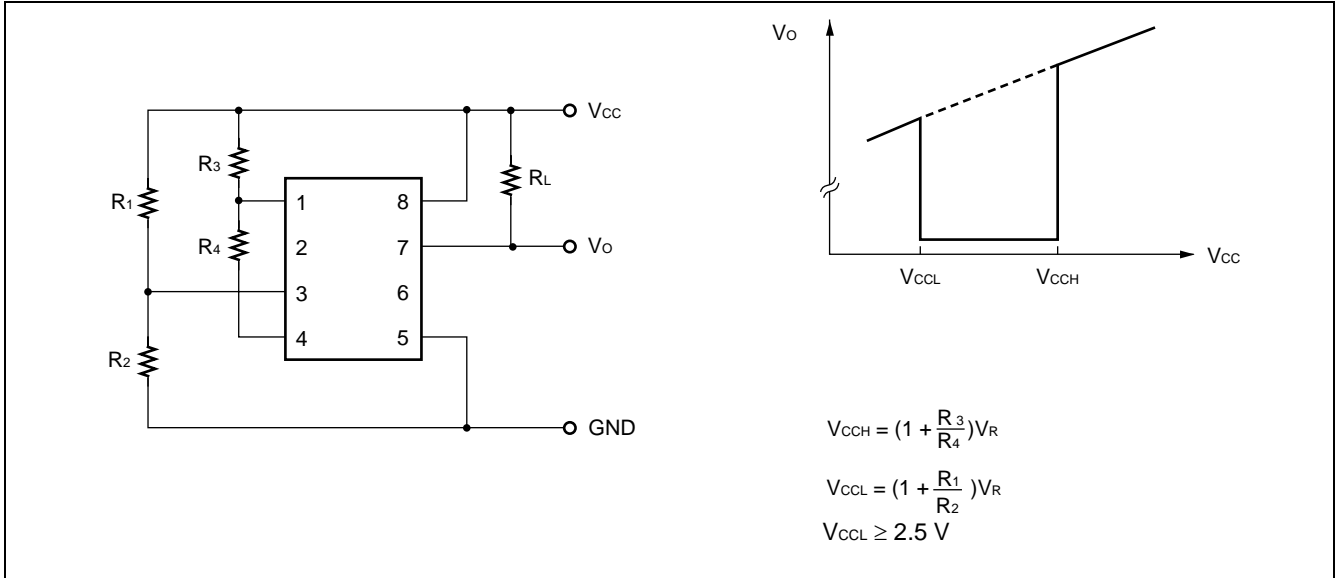
$$V_{CCL} = \left(1 + \frac{R_3}{R_4}\right) V_R$$

$$V_{CCL} \geq 2.5 \text{ V}$$

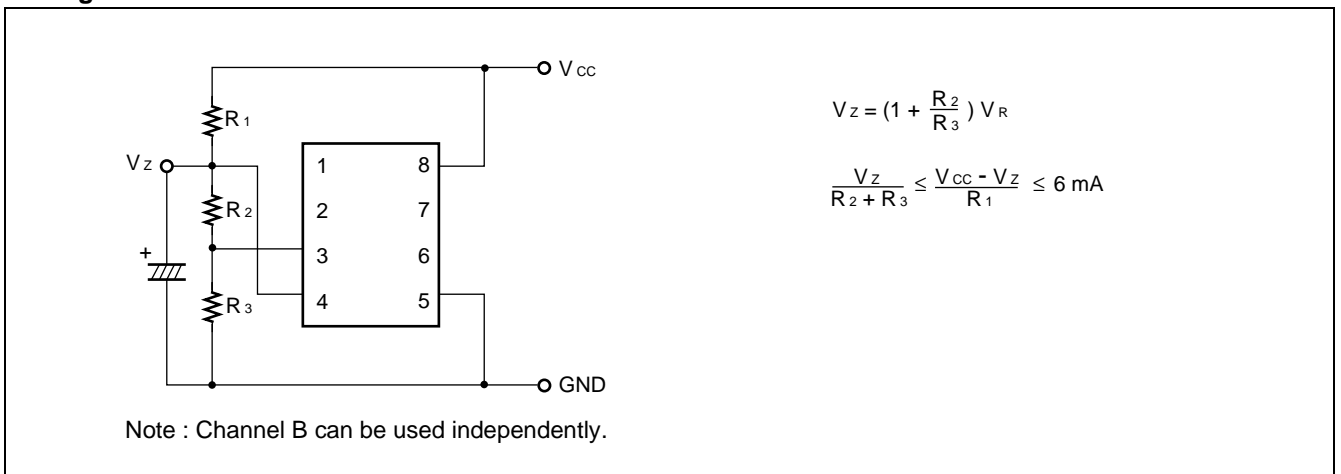
For hysteresis, a positive feedback from pin 2 or 7 is required.

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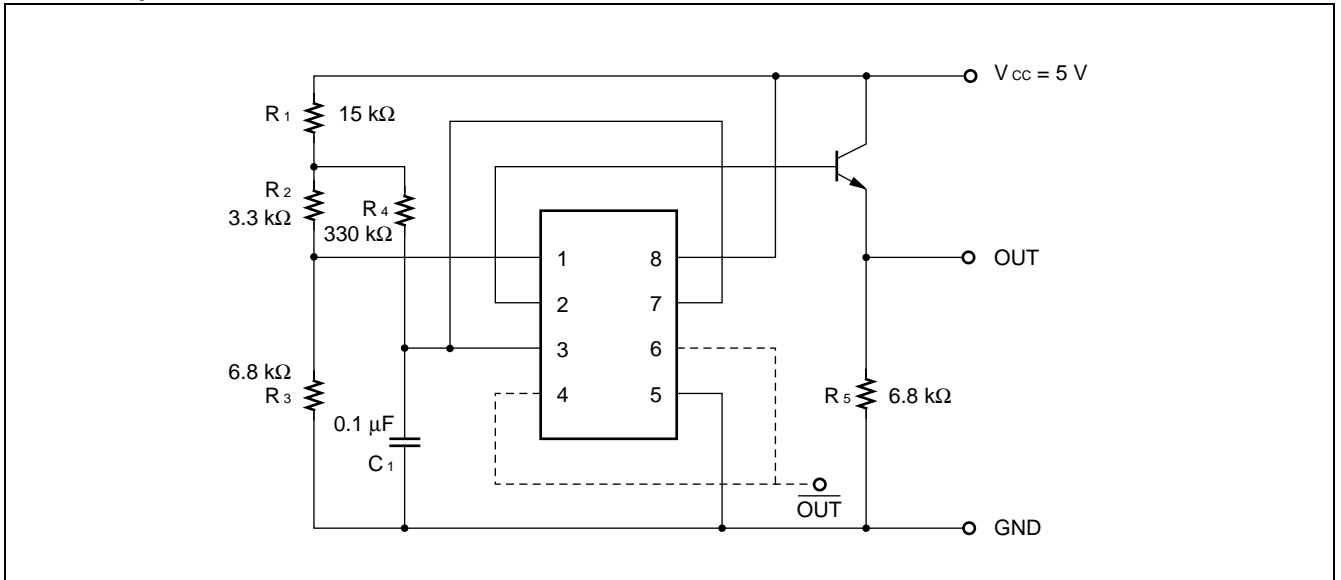
3. Voltage Detection for Alarm



4. Programmable Zener

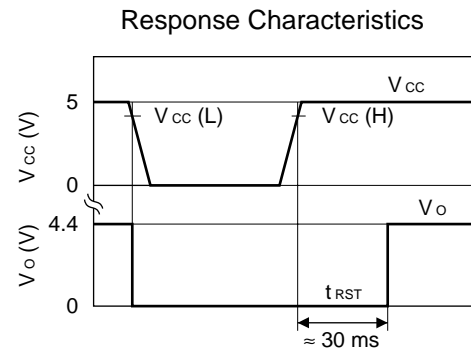
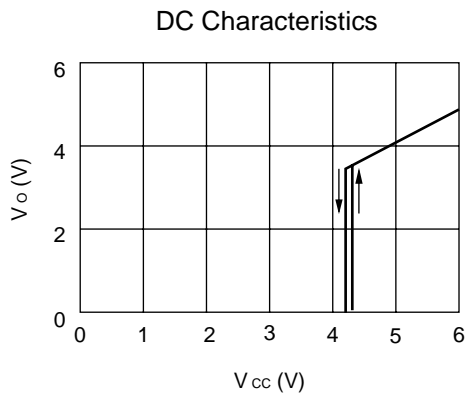


5. Recovery Reset Circuit



MB3761

■ TYPICAL CHARACTERISTICS



- Voltage Threshold Levels (V_{CCL} and V_{CCH}) and Hysteresis Width can be changed by the resistors (R_1 through R_4).

$$V_{CCL} = \frac{R_1 + R_2 + R_3}{R_3} V_{TH}$$

$$V_{CCH} = V_{CCL} + \frac{R_1 (R_2 + R_3)}{R_3 R_4} V_{TH}$$

- Power-On Reset Time is provided by the following approximate equation:

$$t_{RST} = -C_1 R_4 \cdot \ln \left\{ 1 - \frac{V_{TH}}{V_{CC}} \left(1 + \frac{R_1}{R_2 + R_3} \right) \right\}$$

- The recommended value of h_{FE} of the external transistor is from 50 to 200.
- In the case of an instant power fail, the remaining charge in C_1 effects t_{RST} .
- If necessary, the reversed output is provided on HYS terminal

■ NOTES ON USE

- Take account of common impedance when designing the earth line on a printed wiring board.
- Take measures against static electricity.
 - For semiconductors, use antistatic or conductive containers.
 - When storing or carrying a printed circuit board after chip mounting, put it in a conductive bag or container.
 - The work table, tools and measuring instruments must be grounded.
 - The worker must put on a grounding device containing 250 kΩ to 1 MΩ resistors in series.
- Do not apply a negative voltage
 - Applying a negative voltage of -0.3 V or less to an LSI may generate a parasitic transistor, resulting in malfunction.

■ ORDERING INFORMATION

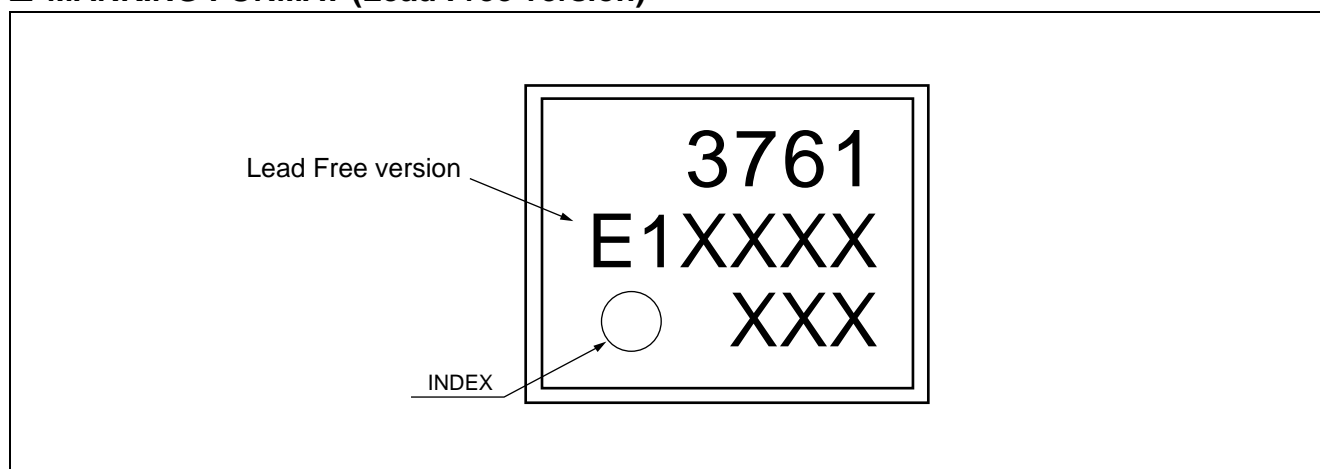
Part number	Package	Remarks
MB3761PF-□□□	8-pin plastic SOP (FPT-8P-M01)	Conventional version
MB3761PF-□□□E1	8-pin plastic SOP (FPT-8P-M01)	Lead Free version

■ RoHS Compliance Information of Lead (Pb) Free version

The LSI products of Fujitsu Microelectronics with "E1" are compliant with RoHS Directive, and has observed the standard of lead, cadmium, mercury, Hexavalent chromium, polybrominated biphenyls (PBB), and polybrominated diphenyl ethers (PBDE).

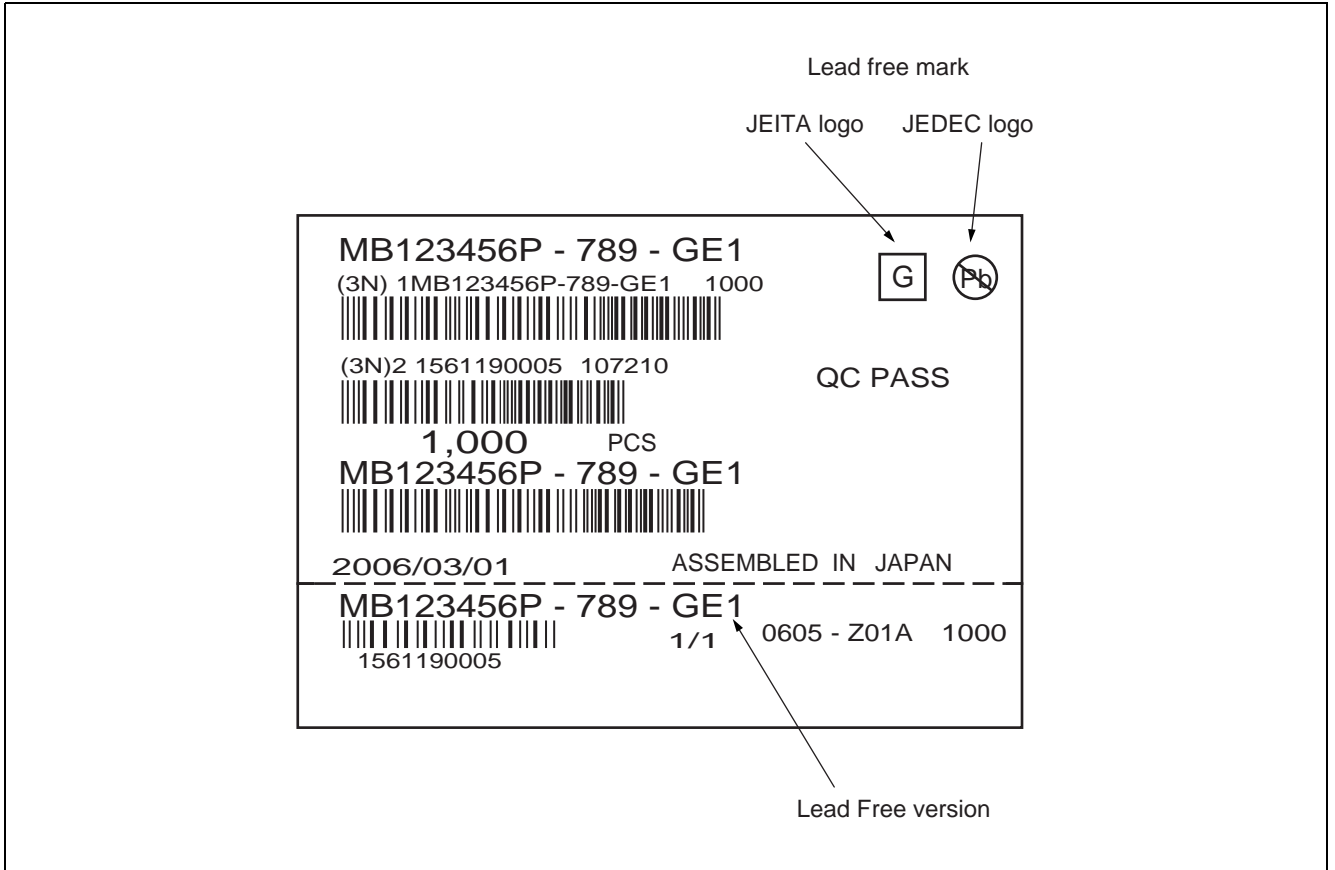
The product that conforms to this standard is added "E1" at the end of the part number.

■ MARKING FORMAT (Lead Free version)



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■ LABELING SAMPLE (Lead free version)

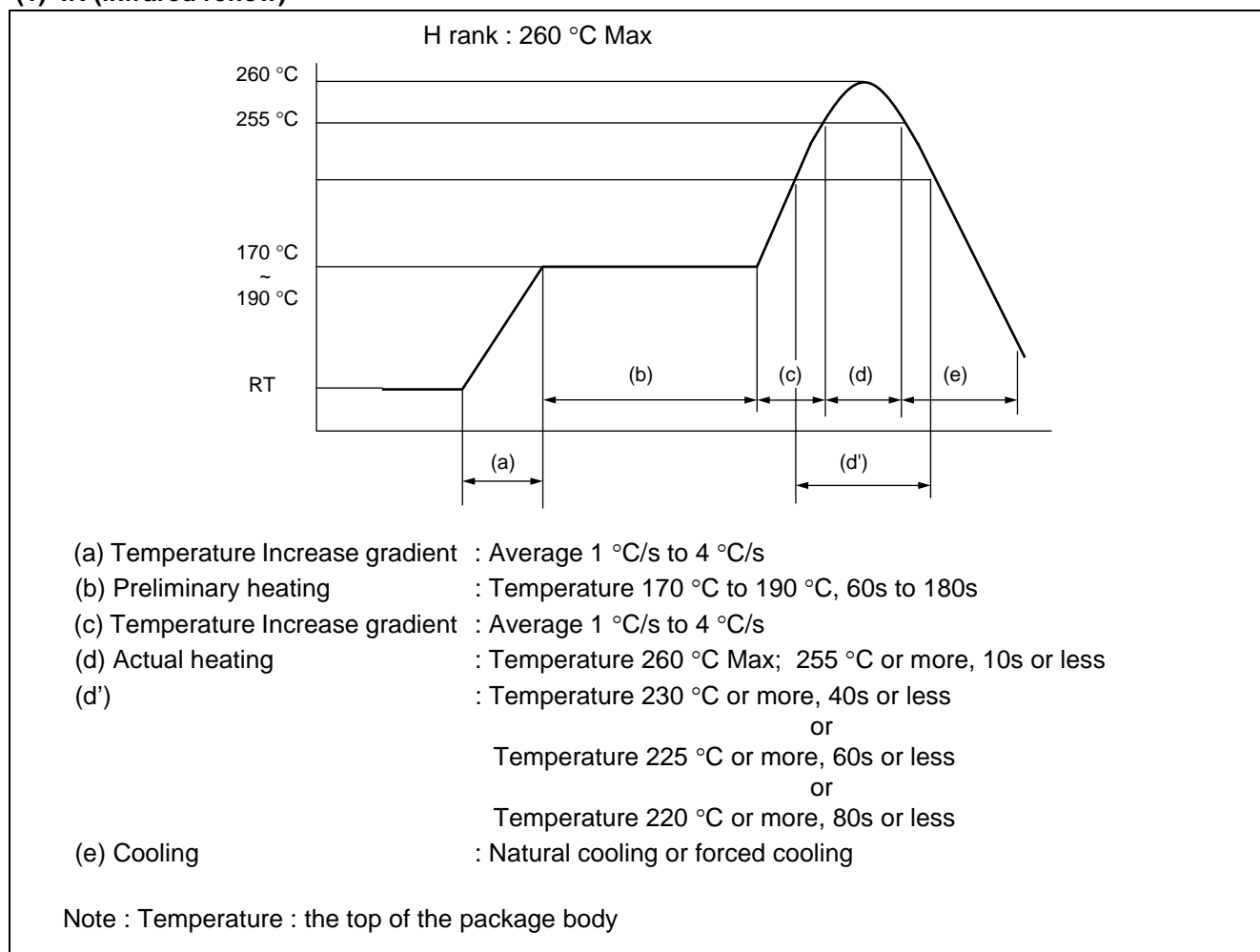


■ MB3761PF-□□□E1 RECOMMENDED CONDITIONS OF MOISTURE SENSITIVITY LEVEL

Item	Condition	
Mounting Method	IR (infrared reflow) , Manual soldering (partial heating method)	
Mounting times	2 times	
Storage period	Before opening	Please use it within two years after Manufacture.
	From opening to the 2nd reflow	Less than 8 days
	When the storage period after opening was exceeded	Please processes within 8 days after baking (125 °C, 24H)
Storage conditions	5 °C to 30 °C, 70%RH or less (the lowest possible humidity)	

[Temperature Profile for FJ Standard IR Reflow]

(1) IR (infrared reflow)



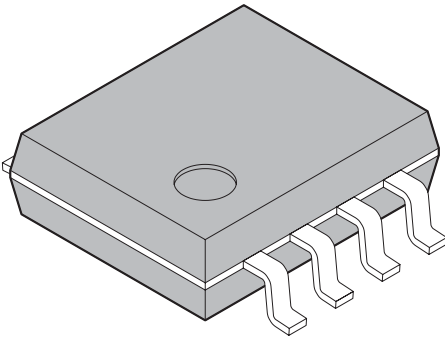
(2) Manual soldering (partial heating method)

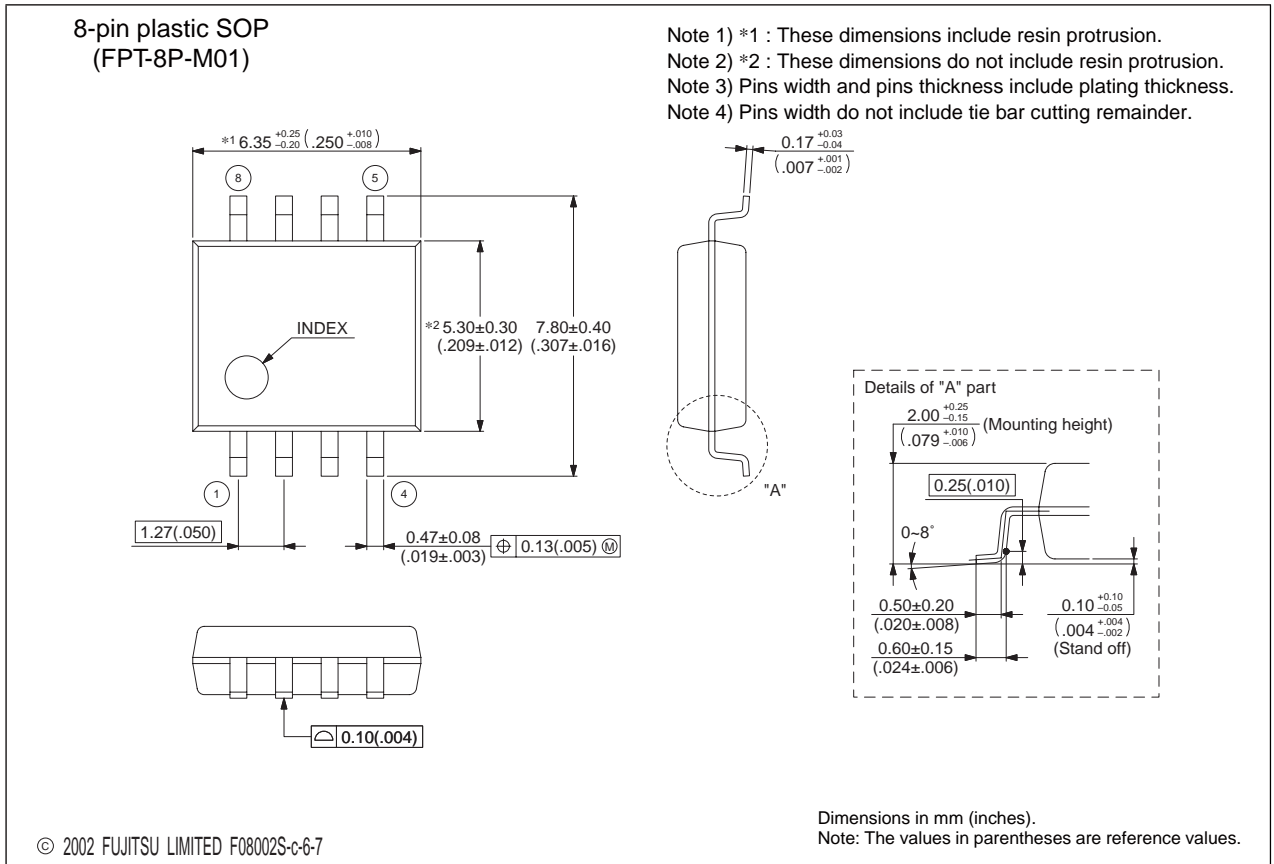
Conditions : Temperature 400 °C Max

Times : 5 s max/pin

MB3761

■ PACKAGE DIMENSION

<p>8-pin plastic SOP</p>  <p>(FPT-8P-M01)</p>	Lead pitch	1.27 mm
	Package width × package length	5.3 × 6.35 mm
	Lead shape	Gullwing
	Sealing method	Plastic mold
	Mounting height	2.25 mm MAX
	Weight	0.10 g
	Code (Reference)	P-SOP8-5.3×6.35-1.27



MEMO

FUJITSU MICROELECTRONICS LIMITED

Shinjuku Dai-Ichi Seimei Bldg. 7-1, Nishishinjuku 2-chome, Shinjuku-ku,
Tokyo 163-0722, Japan Tel: +81-3-5322-3347 Fax: +81-3-5322-3387
<http://jp.fujitsu.com/fml/en/>

For further information please contact:

North and South America

FUJITSU MICROELECTRONICS AMERICA, INC.
1250 E. Arques Avenue, M/S 333
Sunnyvale, CA 94085-5401, U.S.A.
Tel: +1-408-737-5600 Fax: +1-408-737-5999
<http://www.fma.fujitsu.com/>

Asia Pacific

FUJITSU MICROELECTRONICS ASIA PTE LTD.
151 Lorong Chuan, #05-08 New Tech Park,
Singapore 556741
Tel: +65-6281-0770 Fax: +65-6281-0220
<http://www.fujitsu.com/sg/services/micro/semiconductor/>

Europe

FUJITSU MICROELECTRONICS EUROPE GmbH
Pittlerstrasse 47, 63225 Langen,
Germany
Tel: +49-6103-690-0 Fax: +49-6103-690-122
<http://emea.fujitsu.com/microelectronics/>

FUJITSU MICROELECTRONICS SHANGHAI CO., LTD.
Rm.3102, Bund Center, No.222 Yan An Road(E),
Shanghai 200002, China
Tel: +86-21-6335-1560 Fax: +86-21-6335-1605
<http://cn.fujitsu.com/fmc/>

Korea

FUJITSU MICROELECTRONICS KOREA LTD.
206 KOSMO TOWER, 1002 Daechi-Dong,
Kangnam-Gu, Seoul 135-280
Korea
Tel: +82-2-3484-7100 Fax: +82-2-3484-7111
<http://www.fmk.fujitsu.com/>

FUJITSU MICROELECTRONICS PACIFIC ASIA LTD.
10/F., World Commerce Centre, 11 Canton Road
Tsimshatsui, Kowloon
Hong Kong
Tel: +852-2377-0226 Fax: +852-2376-3269
<http://cn.fujitsu.com/fmc/tw>

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